

DESCRIPTION

MEMORY ARRAYS AND METHODS USED IN FORMING A MEMORY ARRAY COMPRISING STRINGS OF MEMORY CELLS

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TECHNICAL FIELD

Embodiments disclosed herein pertain to memory arrays and to methods used in forming a memory array comprising strings of memory cells.

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BACKGROUND

Memory is one type of integrated circuitry and is used in computer systems for storing data. Memory may be fabricated in one or more arrays of individual memory cells. Memory cells may be written to, or read from, using digitlines (which may also be referred to as bitlines, data lines, or sense lines) and access lines (which may also be referred to as wordlines). The sense lines may conductively interconnect memory cells along columns of the array, and the access lines may conductively interconnect memory cells along rows of the array. Each memory cell may be uniquely addressed through the combination of a sense line and an access line.

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Memory cells may be volatile, semi-volatile, or non-volatile. Non-volatile memory cells can store data for extended periods of time in the absence of power. Non-volatile memory is conventionally specified to be memory having a retention time of at least about 10 years. Volatile memory dissipates and is therefore refreshed/rewritten to maintain data storage. Volatile memory may have a retention time of milliseconds or less. Regardless, memory cells are configured to retain or store memory in at least two different selectable states. In a binary system, the states are considered as either a “0” or a “1”. In other systems, at least some individual memory cells may be configured to store more than two levels or states of information.

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A field effect transistor is one type of electronic component that may be used in a memory cell. These transistors comprise a pair of conductive source/drain regions having a semiconductive channel region there-between. A conductive gate is adjacent the channel region and separated there-from by a thin gate insulator. Application of a suitable voltage to the gate allows

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current to flow from one of the source/drain regions to the other through the channel region. When the voltage is removed from the gate, current is largely prevented from flowing through the channel region. Field effect transistors may also include additional structure, for example a reversibly programmable charge-storage region as part of the gate construction between the gate insulator and the conductive gate.

Flash memory is one type of memory and has numerous uses in modern computers and devices. For instance, modern personal computers may have BIOS stored on a flash memory chip. As another example, it is becoming increasingly common for computers and other devices to utilize flash memory in solid state drives to replace conventional hard drives. As yet another example, flash memory is popular in wireless electronic devices because it enables manufacturers to support new communication protocols as they become standardized, and to provide the ability to remotely upgrade the devices for enhanced features.

NAND may be a basic architecture of integrated flash memory. A NAND cell unit comprises at least one selecting device coupled in series to a serial combination of memory cells (with the serial combination commonly being referred to as a NAND string). NAND architecture may be configured in a three-dimensional arrangement comprising vertically-stacked memory cells individually comprising a reversibly programmable vertical transistor. Control or other circuitry may be formed below the vertically-stacked memory cells. Other volatile or non-volatile memory array architectures may also comprise vertically-stacked memory cells that individually comprise a transistor.

Memory arrays may be arranged in memory pages, memory blocks and partial blocks (e.g., sub-blocks), and memory planes, for example as shown and described in any of U.S. Patent Application Publication Nos. 2015/0228659, 2016/0267984, and 2017/0140833, and which are hereby and herein fully incorporated by reference and aspects of which may be used in some embodiments of the inventions disclosed herein. The memory blocks may at least in part define longitudinal outlines of individual wordlines in individual wordline tiers of vertically-stacked memory cells.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a diagrammatic cross-sectional view of a portion of a substrate in process in accordance with an embodiment of the invention and is taken through line 1-1 in Fig. 2.

5 Fig. 2 is a diagrammatic cross-sectional view taken through line 2-2 in Fig. 1.

Figs. 3-13 are diagrammatic sequential sectional and/or enlarged views of the construction of Figs. 1 and 2, or portions thereof, in process in accordance with some embodiments of the invention.

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DETAILED DESCRIPTION OF EXAMPLE EMBODIMENTS

Embodiments of the invention encompass methods used in forming a memory array, for example an array of NAND or other memory cells having peripheral control circuitry under the array (e.g., CMOS-under-array).

15 Embodiments of the invention encompass so-called “gate-last” or “replacement-gate” processing, so-called “gate-first” processing, and other processing whether existing or future-developed independent of when transistor gates are formed. Embodiments of the invention also encompass a memory array (e.g., NAND architecture) independent of method of
20 manufacture. Example method embodiments are described with reference to Figs. 1-13 which may be considered as a “gate-last” or “replacement-gate” process.

Figs. 1 and 2 show a construction 10 having an array or array area 12 in which elevationally-extending strings of transistors and/or memory cells
25 will be formed. Construction 10 comprises a base substrate 11 having any one or more of conductive/conductor/conducting, semiconductive/semiconductor/semiconducting, or insulative/insulator/insulating (i.e., electrically herein) materials. Various materials have been formed elevationally over base substrate 11. Materials
30 may be aside, elevationally inward, or elevationally outward of the Figs. 1 and 2-depicted materials. For example, other partially or wholly fabricated components of integrated circuitry may be provided somewhere above, about, or within base substrate 11. Control and/or other peripheral circuitry for operating components within an array (e.g., array 12) of elevationally-
35 extending strings of memory cells may also be fabricated and may or may

not be wholly or partially within an array or sub-array. Further, multiple sub-arrays may also be fabricated and operated independently, in tandem, or otherwise relative one another. In this document, a “sub-array” may also be considered as an array.

5 A conductor tier 16 comprising conductive material 17 has been formed above substrate 11. Conductor tier 16 may comprise part of control circuitry (e.g., peripheral-under-array circuitry and/or a common source line or plate) used to control read and write access to the transistors and/or memory cells that will be formed within array 12. A stack 18 comprising
10 vertically-alternating insulative tiers 20 and conductive tiers 22 has been formed above conductor tier 16. Example thickness for each of tiers 20 and 22 is 22 to 60 nanometers. Only a small number of tiers 20 and 22 is shown, with more likely stack 18 comprising dozens, a hundred or more, etc. of tiers 20 and 22. Other circuitry that may or may not be part of peripheral
15 and/or control circuitry may be between conductor tier 16 and stack 18. For example, multiple vertically-alternating tiers of conductive material and insulative material of such circuitry may be below a lowest of the conductive tiers 22 and/or above an uppermost of the conductive tiers 22. For example, one or more select gate tiers (not shown) may be between
20 conductor tier 16 and the lowest conductive tier 22 and one or more select gate tiers may be above an uppermost of conductive tiers 22. Regardless, conductive tiers 22 (alternately referred to as first tiers) may not comprise conducting material and insulative tiers 20 (alternately referred to as second tiers) may not comprise insulative material or be insulative at this point in
25 processing in conjunction with the hereby initially-described example method embodiment which is “gate-last” or “replacement-gate”. Example conductive tiers 22 comprise first material 26 (e.g., silicon nitride) which may be wholly or partially sacrificial. Example insulative tiers 20 comprise second material 24 (e.g., silicon dioxide) that is of different composition
30 from that of first material 26 and which may be wholly or partially sacrificial.

 Channel openings 25 have been formed (e.g., by etching) through insulative tiers 20 and conductive tiers 22 to conductor tier 16. In some embodiments, channel openings 25 may go partially into conductive material
35 17 of conductor tier 16 as shown or may stop there-atop (not shown).

Alternately, as an example, channel openings 25 may stop atop or within the lowest insulative tier 20. A reason for extending channel openings 25 at least to conductive material 17 of conductor tier 16 is to assure direct electrical coupling of subsequently-formed channel material (not yet shown) to conductor tier 16 without using alternative processing and structure to do so when such a connection is desired. Etch-stop material (not shown) may be within or atop conductive material 17 of conductor tier 16 to facilitate stopping of the etching of channel openings 25 relative to conductor tier 16 when such is desired. Such etch-stop material may be sacrificial or non-sacrificial. By way of example and for brevity only, channel openings 25 are shown as being arranged in groups or columns of staggered rows of four and five openings 25 per row and being arrayed in laterally-spaced memory-block regions 58 that will comprise laterally-spaced memory blocks 58 in a finished circuitry construction. In this document, “block” is generic to include “sub-block”. Memory-block regions 58 and resultant memory blocks 58 (not yet shown) may be considered as being longitudinally elongated and oriented, for example along a direction 55. Memory-block regions 58 may otherwise not be discernable at this point of processing. Any alternate existing or future-developed arrangement and construction may be used.

Transistor channel material may be formed in the individual channel openings elevationally along the insulative tiers and the conductive tiers, thus comprising individual channel-material strings, which is directly electrically coupled with conductive material in the conductor tier.

Individual memory cells of the example memory array being formed may comprise a gate region (e.g., a control-gate region) and a memory structure laterally between the gate region and the channel material. In one such embodiment, the memory structure is formed to comprise a charge-blocking region, storage material (e.g., charge-storage material), and an insulative charge-passage material. The storage material (e.g., floating gate material such as doped or undoped silicon or charge-trapping material such as silicon nitride, metal dots, etc.) of the individual memory cells is elevationally along individual of the charge-blocking regions. The insulative charge-passage material (e.g., a band gap-engineered structure having nitrogen-containing material [e.g., silicon nitride] sandwiched between two

insulator oxides [e.g., silicon dioxide]) is laterally between the channel material and the storage material.

Figs. 3, 3A, 4 and 4A show one embodiment wherein charge-blocking material 30, storage material 32, and charge-passage material 34 have been
5 formed in individual channel openings 25 elevationally along insulative tiers 20 and conductive tiers 22. Transistor materials 30, 32, and 34 (e.g., memory cell materials) may be formed by, for example, deposition of respective thin layers thereof over stack 18 and within individual channel openings 25 followed by planarizing such back at least to a top surface of
10 stack 18. Channel material 36 has also been formed in channel openings 25 elevationally along insulative tiers 20 and conductive tiers 22, thus comprising individual operative channel-material strings 53. Materials 30, 32, 34, and 36 are collectively shown as and only designated as material 37 in Figs. 3 and 4 due to scale. Example channel materials 36 include
15 appropriately-doped crystalline semiconductor material, such as one or more silicon, germanium, and so-called III/V semiconductor materials (e.g., GaAs, InP, GaP, and GaN). Example thickness for each of materials 30, 32, 34, and 36 is 25 to 100 Angstroms. Punch etching may be conducted as shown to remove materials 30, 32, and 34 from the bases of channel
20 openings 25 to expose conductor tier 16 such that channel material 36 is directly against conductive material 17 of conductor tier 16. Such punch etching may occur separately with respect to each of materials 30, 32, and 34 (as shown) or may occur collectively with respect to all after deposition of material 34 (not shown). Alternately, and by way of example only, no
25 punch etching may be conducted and channel material 36 may be directly electrically coupled to conductive material 17 of conductor tier 16 by a separate conductive interconnect (not shown). Channel openings 25 are shown as comprising a radially-central solid dielectric material 38 (e.g., spin-on-dielectric, silicon dioxide, and/or silicon nitride). Alternately, and
30 by way of example only, the radially-central portion within channel openings 25 may include void space(s) (not shown) and/or be devoid of solid material (not shown). Conductive plugs (not shown) may be formed atop channel material strings 53 for better conductive connection to overlying circuitry (not shown).

Referring to Figs. 5 and 6, horizontally-elongated trenches 40 have been formed (e.g., by anisotropic etching) into stack 18 to form laterally-spaced memory-block regions 58. Horizontally-elongated trenches 40 may have respective bottoms that are directly against conductive material 17 (e.g., atop or within) of conductor tier 16 (as shown) or may have respective bottoms that are above conductive material 17 of conductor tier 16 (not shown). Horizontally-elongated trenches 40 may be considered as comprising sides 45.

The above processing shows forming and filling channel openings 25 prior to forming trenches 40. Such could be reversed. Alternately, trenches 40 could be formed in between the forming and filling of channel openings 25 (not ideal).

Referring to Figs. 7-9, and in one embodiment, material 26 (not shown) of conductive tiers 22 has been removed, for example by being isotropically etched away through trenches 40 ideally selectively relative to the other exposed materials (e.g., using liquid or vapor H_3PO_4 as a primary etchant where material 26 is silicon nitride, and other materials comprise one or more oxides or polysilicon). Material 26 in conductive tiers 22 in the example embodiment is sacrificial and has been replaced with conducting material 48, and which has thereafter been removed from trenches 40, thus forming individual conductive lines 29 (e.g., wordlines) and elevationally-extending strings 49 of individual transistors and/or memory cells 56. Conducting material 48 may be laterally-recessed back within conductive tiers 22 from trench sides 45 (as shown) to assure vertical separation of individual conductive lines 29 relative one another. A thin insulative liner (e.g., Al_2O_3 and not shown) may be formed before forming conducting material 48.

Approximate locations of transistors and/or memory cells 56 are indicated with a bracket in Fig. 9 and some with dashed outlines in Figs. 7 and 8, with transistors and/or memory cells 56 being essentially ring-like or annular in the depicted example. Alternately, transistors and/or memory cells 56 may not be completely encircling relative to individual channel openings 25 such that each channel opening 25 may have two or more elevationally-extending strings 49 (e.g., multiple transistors and/or memory cells about individual channel openings in individual conductive tiers with

perhaps multiple wordlines per channel opening in individual conductive tiers, and not shown). Conducting material 48 may be considered as having terminal ends 50 (Fig. 9) corresponding to control-gate regions 52 of individual transistors and/or memory cells 56. Control-gate regions 52 in the depicted embodiment comprise individual portions of individual conductive lines 29. Materials 30, 32, and 34 may be considered as a memory structure 65 that is laterally between control-gate region 52 and channel material 36. In one embodiment and as shown with respect to the example “gate-last” processing, conducting material 48 of conductive tiers 22 is formed after forming trenches 40. Alternately, the conducting material of the conductive tiers may be formed before forming trenches 40 (not shown) and/or before forming channel openings 25, for example with respect to “gate-first” processing.

A charge-blocking region (e.g., charge-blocking material 30) is between storage material 32 and individual control-gate regions 52. A charge block may have the following functions in a memory cell: In a program mode, the charge block may prevent charge carriers from passing out of the storage material (e.g., floating-gate material, charge-trapping material, etc.) toward the control gate, and in an erase mode the charge block may prevent charge carriers from flowing into the storage material from the control gate. Accordingly, a charge block may function to block charge migration between the control-gate region and the storage material of individual memory cells. An example charge-blocking region as shown comprises insulator material 30. By way of further examples, a charge-blocking region may comprise a laterally (e.g., radially) outer portion of the storage material (e.g., material 32) where such storage material is insulative (e.g., in the absence of any different-composition material between an insulative storage material 32 and conducting material 48). Regardless, as an additional example, an interface of a storage material and conductive material of a control gate may be sufficient to function as a charge-blocking region in the absence of any separate-composition-insulator material 30. Further, an interface of conducting material 48 with material 30 (when present) in combination with insulator material 30 may together function as a charge-blocking region, and as alternately or additionally may a laterally-outer region of an insulative storage material (e.g., a silicon nitride material

32). An example material 30 is one or more of silicon hafnium oxide and silicon dioxide.

A wall is formed in individual of the trenches laterally-between immediately-laterally-adjacent of the memory-block regions, for example
5 and in some embodiments as is described with reference to Figs. 10-13.

Referring to Fig. 10, sides 45 of trenches 40 have been lined with insulative material 70 that comprises at least one of an insulative nitride and elemental-form boron. In one embodiment, the insulative material comprises an insulative nitride, in one embodiment elemental-form boron,
10 and in one embodiment both. In one embodiment, the insulative nitride comprises one or more of silicon nitride, boron nitride, carbon nitride, silicon nitride carbide, and germanium nitride. In one embodiment and as shown, the at least one of insulative nitride and elemental-form boron is formed directly against conducting material 48 of conductive lines 29 and in
15 one embodiment is devoid (i.e., from 0 to no more than 0.1 atomic percent) of oxygen. Some prior art methods and constructions formed silicon dioxide directly against elemental-form-tungsten-conducting material 48 which undesirably caused formation of tungsten oxide. Using an insulative material comprising an insulative nitride and/or elemental-form boron,
20 particularly where the insulative material is devoid of oxygen, may at least reduce or even eliminate oxide formation.

In one embodiment, individual trenches 40 are formed to have an uppermost minimum lateral width in a vertical cross-section, for example such width W in the vertical cross-section that is the plane of the page upon
25 which Fig. 10 lies. In such embodiment, insulative material 70 on each side of core material 57 has a lateral width of 1% to 20% of uppermost minimum lateral width W in the vertical cross-section.

Referring to Figs. 11 and 12, a core material 57 has been formed in trenches 40 to span laterally-between the at least one of the insulative
30 nitride and the elemental-form boron 70, thus forming a wall 75 in individual trenches 40 laterally-between immediately-laterally-adjacent memory-block regions 58. In one embodiment and as shown, core material 57 is formed directly against the at least one of the insulative nitride and the elemental-form boron. In one embodiment, core material 57 at least
35 predominately (i.e., more than 50 up to and including 100 atomic percent)

comprises insulative material, in another embodiment at least predominately comprises conductive material, and in still another embodiment at least predominately comprises semiconductive material. Example conductive materials include metal material and conductively-doped semiconductive material, for example conductively-doped elemental-form silicon, conductively-doped elemental-form germanium, a conductively-doped alloy of silicon and germanium, conductive elemental metals (e.g., W) conductive metal nitrides (e.g., TiN), and conductive metal oxides (e.g., indium oxide, ruthenium oxide, etc.). Example insulative core materials include insulative oxides, for example aluminum oxide, silicon dioxide, tantalum oxide, cupric oxide, cuprous oxide, iron oxide, and ferroelectric oxides. Example semiconductive materials include undoped or semiconductively-doped elemental-form silicon, undoped or semiconductively-doped elemental-form germanium, and an undoped or semiconductively-doped alloy of silicon and germanium.

In one embodiment, core material 57 is homogenous. In another embodiment, core material 57 is not homogenous. For example, and by way of example only, core material 57 may comprise a laterally-outer insulative oxide (e.g., any of those stated above) and a laterally-inner material (i.e., laterally inward thereof) that is not an insulative oxide (e.g., any one or more of insulative, conductive, and semiconductive materials as described above). Further, core material 57 may comprise void space (not shown), for example having one or more void spaces of any size or shape internally there-within (not shown). In one ideal embodiment, insulative material 70 comprises silicon nitride directly against conducting material 48 and core material 57 comprises laterally-outer silicon dioxide directly (the same, less, or greater thickness as insulative material 70) against the silicon nitride and laterally-inner undoped or lightly-doped (ideally not conductively doped) polysilicon directly against the silicon dioxide.

Fig. 13 shows subsequent processing whereby materials 70 and 57 have been planarized back at least to an elevationally outermost surface of stack 18, thereby forming the example-finished-construction walls 75 within trenches 40.

Alternate embodiment constructions may result from method embodiments described above, or otherwise. Regardless, embodiments of

the invention encompass memory arrays independent of method of manufacture. Nevertheless, such memory arrays may have any of the attributes as described herein in method embodiments. Likewise, the above-described method embodiments may incorporate, form, and/or have any of the attributes described with respect to device embodiments.

Embodiments of the invention include a memory array (e.g., 12) comprising strings of memory cells. The memory array comprises a vertical stack (e.g., 18) comprising alternating insulative tiers (e.g., 20) and conductive tiers (e.g., 22). The conductive tiers individually comprise conductive lines (e.g., 29). Strings (e.g., 49) of memory cells (e.g., 56) in the stack comprise channel material (e.g., 36) extending through the insulative tiers and the conductive tiers. Individual of the memory cells comprise the channel material, a gate region (e.g., 52) that is part of one of the conductive lines in individual of the conductive tiers, and a memory structure (e.g., 65) laterally-between the gate region and the channel material in the individual conductive tiers.

Walls (e.g., 75) individually extend through the insulative tiers and the conductive tiers laterally between immediately-adjacent of the conductive lines. The walls individually comprise laterally-outer insulative material (e.g., 70) and a core material (e.g., 57) spanning laterally-between the laterally-outer insulative material. The laterally-outer insulative material comprises at least one of an insulative nitride and elemental-form boron.

Any other attribute(s) or aspect(s) as shown and/or described herein with respect to other embodiments may be used.

The above processing(s) or construction(s) may be considered as being relative to an array of components formed as or within a single stack or single deck of such components above or as part of an underlying base substrate (*albeit*, the single stack/deck may have multiple tiers). Control and/or other peripheral circuitry for operating or accessing such components within an array may also be formed anywhere as part of the finished construction, and in some embodiments may be under the array (e.g., CMOS under-array). Regardless, one or more additional such stack(s)/deck(s) may be provided or fabricated above and/or below that shown in the figures or described above. Further, the array(s) of components may be the same or

different relative one another in different stacks/decks and different stacks/decks may be of the same thickness or of different thicknesses relative one another. Intervening structure may be provided between immediately-vertically-adjacent stacks/decks (e.g., additional circuitry and/or dielectric layers). Also, different stacks/decks may be electrically coupled relative one another. The multiple stacks/decks may be fabricated separately and sequentially (e.g., one atop another), or two or more stacks/decks may be fabricated at essentially the same time.

The assemblies and structures discussed above may be used in integrated circuits/circuitry and may be incorporated into electronic systems. Such electronic systems may be used in, for example, memory modules, device drivers, power modules, communication modems, processor modules, and application-specific modules, and may include multilayer, multichip modules. The electronic systems may be any of a broad range of systems, such as, for example, cameras, wireless devices, displays, chip sets, set top boxes, games, lighting, vehicles, clocks, televisions, cell phones, personal computers, automobiles, industrial control systems, aircraft, etc.

In this document unless otherwise indicated, “elevational”, “higher”, “upper”, “lower”, “top”, “atop”, “bottom”, “above”, “below”, “under”, “beneath”, “up”, and “down” are generally with reference to the vertical direction. “Horizontal” refers to a general direction (i.e., within 10 degrees) along a primary substrate surface and may be relative to which the substrate is processed during fabrication, and vertical is a direction generally orthogonal thereto. Reference to “exactly horizontal” is the direction along the primary substrate surface (i.e., no degrees there-from) and may be relative to which the substrate is processed during fabrication. Further, “vertical” and “horizontal” as used herein are generally perpendicular directions relative one another and independent of orientation of the substrate in three-dimensional space. Additionally, “elevationally-extending” and “extend(ing) elevationally” refer to a direction that is angled away by at least 45° from exactly horizontal. Further, “extend(ing) elevationally”, “elevationally-extending”, “extend(ing) horizontally”, “horizontally-extending” and the like with respect to a field effect transistor are with reference to orientation of the transistor’s channel length along which current flows in operation between the source/drain regions. For

bipolar junction transistors, “extend(ing) elevationally” “elevationally-extending”, “extend(ing) horizontally”, “horizontally-extending” and the like, are with reference to orientation of the base length along which current flows in operation between the emitter and collector. In some embodiments, any component, feature, and/or region that extends elevationally extends vertically or within 10° of vertical.

Further, “directly above”, “directly below”, and “directly under” require at least some lateral overlap (i.e., horizontally) of two stated regions/materials/components relative one another. Also, use of “above” not preceded by “directly” only requires that some portion of the stated region/material/component that is above the other be elevationally outward of the other (i.e., independent of whether there is any lateral overlap of the two stated regions/materials/components). Analogously, use of “below” and “under” not preceded by “directly” only requires that some portion of the stated region/material/component that is below/under the other be elevationally inward of the other (i.e., independent of whether there is any lateral overlap of the two stated regions/materials/components).

Any of the materials, regions, and structures described herein may be homogenous or non-homogenous, and regardless may be continuous or discontinuous over any material which such overlie. Where one or more example composition(s) is/are provided for any material, that material may comprise, consist essentially of, or consist of such one or more composition(s). Further, unless otherwise stated, each material may be formed using any suitable existing or future-developed technique, with atomic layer deposition, chemical vapor deposition, physical vapor deposition, epitaxial growth, diffusion doping, and ion implanting being examples.

Additionally, “thickness” by itself (no preceding directional adjective) is defined as the mean straight-line distance through a given material or region perpendicularly from a closest surface of an immediately-adjacent material of different composition or of an immediately-adjacent region. Additionally, the various materials or regions described herein may be of substantially constant thickness or of variable thicknesses. If of variable thickness, thickness refers to average thickness unless otherwise indicated, and such material or region will have some minimum thickness and some

maximum thickness due to the thickness being variable. As used herein, “different composition” only requires those portions of two stated materials or regions that may be directly against one another to be chemically and/or physically different, for example if such materials or regions are not
5 homogenous. If the two stated materials or regions are not directly against one another, “different composition” only requires that those portions of the two stated materials or regions that are closest to one another be chemically and/or physically different if such materials or regions are not homogenous. In this document, a material, region, or structure is “directly against”
10 another when there is at least some physical touching contact of the stated materials, regions, or structures relative one another. In contrast, “over”, “on”, “adjacent”, “along”, and “against” not preceded by “directly” encompass “directly against” as well as construction where intervening material(s), region(s), or structure(s) result(s) in no physical touching
15 contact of the stated materials, regions, or structures relative one another.

Herein, regions-materials-components are “electrically coupled” relative one another if in normal operation electric current is capable of continuously flowing from one to the other and does so predominately by movement of subatomic positive and/or negative charges when such are
20 sufficiently generated. Another electronic component may be between and electrically coupled to the regions-materials-components. In contrast, when regions-materials-components are referred to as being “directly electrically coupled”, no intervening electronic component (e.g., no diode, transistor, resistor, transducer, switch, fuse, etc.) is between the directly electrically
25 coupled regions-materials-components.

Any use of “row” and “column” in this document is for convenience in distinguishing one series or orientation of features from another series or orientation of features and along which components have been or may be formed. “Row” and “column” are used synonymously with respect to any
30 series of regions, components, and/or features independent of function. Regardless, the rows may be straight and/or curved and/or parallel and/or not parallel relative one another, as may be the columns. Further, the rows and columns may intersect relative one another at 90° or at one or more other angles.

The composition of any of the conductive/conductor/conducting materials herein may be metal material and/or conductively-doped semiconductive/semiconductor/semiconducting material. “Metal material” is any one or combination of an elemental metal, any mixture or alloy of two or more elemental metals, and any one or more conductive metal compound(s).

Herein, any use of “selective” as to etch, etching, removing, removal, depositing, forming, and/or formation is such an act of one stated material relative to another stated material(s) so acted upon at a rate of at least 2:1 by volume. Further, any use of selectively depositing, selectively growing, or selectively forming is depositing, growing, or forming one material relative to another stated material or materials at a rate of at least 2:1 by volume for at least the first 75 Angstroms of depositing, growing, or forming.

Unless otherwise indicated, use of “or” herein encompasses either and both.

CONCLUSION

In some embodiments, a method used in forming a memory array comprising strings of memory cells comprises forming a stack comprising vertically-alternating first tiers and second tiers. Horizontally-elongated trenches are formed into the stack to form laterally-spaced memory-block regions. A wall is formed in individual of the trenches laterally-between immediately-laterally-adjacent of the memory-block regions. The forming of the wall comprises lining sides of the trenches with insulative material comprising at least one of an insulative nitride and elemental-form boron. A core material is formed in the trenches to span laterally-between the at least one of the insulative nitride and the elemental-form boron.

In some embodiments, a method used in forming a memory array comprising strings of memory cells comprises forming a stack comprising vertically-alternating first tiers and second tiers. Horizontally-elongated trenches are formed into the stack to form laterally-spaced memory-block regions. Through the trenches, sacrificial material that is in the first tiers is isotropically etched away and replaced with conducting material of individual conductive lines. Individual memory cells of the strings of memory cells are formed to comprise channel material of channel-material

strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the first tiers, and a memory structure laterally-between the gate region and the channel material of the channel-material strings in the individual first tiers. The channel-material strings are formed before forming the conducting material of the individual conductive lines. After the replacing, a wall in individual of the trenches is formed laterally-between immediately-laterally-adjacent of the memory-block regions. The forming of the wall comprises lining sides of the trenches with insulative material comprising at least one of an insulative nitride and elemental-form boron that is directly against the conducting material of the individual conductive lines. A core material is formed in the trenches spanning laterally between the at least one of the insulative nitride and the elemental-form boron. The forming of the core material comprises forming a laterally-outer silicon dioxide that is directly against said at least one of insulative nitride and elemental-form boron. Polysilicon is formed directly against and spans laterally-between said laterally-outer silicon dioxide.

In some embodiments, a memory array comprising strings of memory cells comprises a vertical stack comprising alternating insulative tiers and conductive tiers. The conductive tiers individually comprise conductive lines. Strings of memory cells in the stack comprise channel material that extends through the insulative tiers and the conductive tiers. Individual of the memory cells comprise the channel material, a gate region that is part of one of the conductive lines in individual of the conductive tiers, and a memory structure laterally-between the gate region and the channel material in the individual conductive tiers. Walls individually extend through the insulative tiers and the conductive tiers laterally between immediately-adjacent of the conductive lines. The walls individually comprise laterally-outer insulative material and a core material spanning laterally-between the laterally-outer insulative material. The laterally-outer insulative material comprises at least one of an insulative nitride and elemental-form boron.

In some embodiments, a memory array comprising strings of memory cells comprises a vertical stack comprising alternating insulative tiers and conductive tiers. The conductive tiers individually comprise conductive

lines comprising conducting material. Strings of memory cells in the stack comprise channel material that extends through the insulative tiers and the conductive tiers. Individual of the memory cells comprise the channel material, a gate region that is part of one of the conductive lines in

5 individual of the conductive tiers, and a memory structure laterally-between the gate region and the channel material in the individual conductive tiers. Walls individually extend through the insulative tiers and the conductive tiers laterally-between two of the conductive lines. The walls individually comprise laterally-outer insulative material and a core material spanning

10 laterally-between the laterally-outer insulative material. The laterally-outer insulative material comprises at least one of an insulative nitride and elemental-form boron that is directly against the conducting material of the conductive lines. The core material comprises a laterally-outer silicon dioxide that is directly against said at least one of insulative nitride and

15 elemental-form boron. Polysilicon is directly against and spans laterally-between said laterally-outer silicon dioxide.

CLAIMS:

1. A method used in forming a memory array comprising strings of memory cells, comprising:
 - 5 forming a stack comprising vertically-alternating first tiers and second tiers;
forming horizontally-elongated trenches into the stack to form laterally-spaced memory-block regions;
forming a wall in individual of the trenches laterally-between
 - 10 immediately laterally adjacent of the laterally-spaced memory-block regions, the forming of the wall comprising:
 - lining sides and bottoms of trenches with a layer of insulative material comprising an insulative nitride, an elemental-form boron, or both; and
 - 15 forming a core material in the trenches to span laterally, wherein the layer of insulative material surrounds the core material at the sides and the bottoms of the trenches completely.
- 20 2. The method of claim 1 wherein the layer of insulative material comprises one of more members of the group consisting of silicon nitride, boron nitride, carbon nitride, silicon nitride carbide, and germanium nitride.
- 25 3. The method of claim 1 wherein the layer of insulative material is devoid of oxygen.

4. The method of claim 1 comprising:

before forming the wall in the individual trenches, isotropically etching away and replacing sacrificial material that is in the first tiers with conducting material of individual conductive lines;

5 forming individual memory cells of the strings of memory cells to comprise channel material of channel-material strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the first tiers, and a memory structure laterally-between the gate region and the channel material of the channel-material strings in the individual first tiers, forming the channel-material strings before forming the conducting material of the individual conductive lines; and
10 after the replacing, forming the wall in the individual trenches.

5. The method of claim 1,

15 wherein the individual trenches having an uppermost minimum lateral width in a vertical cross-section, the insulative material layer on each side of the core material having a lateral width of 1% to 20% of the uppermost minimum lateral width in the vertical cross-section.

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6. A method used in forming a memory array comprising strings of memory cells, comprising:

forming a stack comprising vertically-alternating first tiers and second tiers;

25 forming horizontally-elongated trenches into the stack to form laterally-spaced memory-block regions;

through the trenches, isotropically etching away and replacing sacrificial material that is in the first tiers with conducting material of individual conductive lines;

forming individual memory cells of the strings of memory cells to comprise channel material of channel-material strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the first tiers, and a memory structure laterally-between the

5 gate region and the channel material of the channel-material strings in the individual first tiers, forming the channel-material strings before forming the conducting material of the individual conductive lines;

after the replacing, forming a wall in individual of the trenches laterally-between immediately adjacent of the laterally-spaced memory-

10 block regions, the forming of the wall comprising;

lining sides and bottoms of the trenches with a layer of insulative material comprising an insulative nitride, an elemental-form boron, or both, wherein the layer of insulative material is directly against the conducting material of the individual conductive lines; and

15 forming a core material in the trenches spanning laterally, wherein the layer of insulative material surrounds the core material at the sides and the bottoms of the trenches completely, the forming of the core material comprising:

forming a laterally-outer silicon dioxide that is directly against the

20 layer of insulative material; and

forming polysilicon directly against and to span laterally-between said laterally-outer silicon dioxide.